

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	9253	((438/150) or (257/74) or (257/E27.026) or (257/E27.112) or (438/198) or (438/285) or (438/455) or (438/459) or (438/479)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/18 10:42
L4	861	257/903	USPAT	OR	ON	2007/09/18 11:14
L6	606	(257/627).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/18 11:16
L7	936	(257/903).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/18 11:14
L8	396	(257/627).CCLS.	USPAT	OR	OFF	2007/09/18 11:16
S4	5	("5976953") or ("6544837") or ("6624046") or ("6509639") or ("5880010").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/02/20 16:45
S5	1	("20030148590").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/02/20 16:46
S7	6	("6974653") or ("6563131") or ("6700163") or ("6943405") or ("6965503") or ("6881672").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/02/20 16:49
S8	10	("6670677") or ("6590258") or ("5057898") or ("6124615") or ("6355501") or ("5889302") or ("5426072") or ("20030094674") or ("20040144979") or ("20040146701").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/02/20 17:18
S9	1269	(257/713).CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2006/02/20 17:13
S10	1247	(257/701).CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2006/02/20 17:13
S11	1645	(257/700).CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2006/02/20 17:13
S12	3905	((257/700) or (257/713) or (257/701)).CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2006/02/20 17:14
S13	0	S12 and (crystal near orientation) and pFET and nFET	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 17:15

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S14	0	S12 and pFET and nFET	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 17:15
S15	7	S12 and (crystal near orientation)	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 17:16
S16	9	S12 and PMOS and NMOS	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 17:16
S17	5	S8 and orientation	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 17:18
S18	33	("4996574" "5321286" "5346834" "5420048" "5451798" "5482877" "5497019" "5581101" "5612552" "5675185" "5689136").PN. OR ("5889302").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:22
S19	11902	crystal adj orientation	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:22
S20	3242	S19 and inventor	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:22
S21	617	S19 and inventor and insulat\$3 near layer	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:23
S22	644	S19 and inventor and insulat\$3 near (layer region)	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:38
S23	7	"6429085"	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:35
S24	27	"4692994"	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:35
S25	54	"4768076"	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:35
S26	31	"5006913"	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:36
S27	589	S19 and inventor and (insulat\$3 near (layer region)) and ((<100> "[100]" "<110>" "[110]"))	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:47
S28	266	S19 and inventor and (insulat\$3 near (layer region)) and ((<100> "[100]" "<110>" "[110]")) and conductivity	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:47
S29	32	S19 and inventor and (insulat\$3 near (layer region)) and ((<100> "[100]" "<110>" "[110]")) and second near conductivity	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:41

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S30	2	S19 and inverter and (insulat\$3 near (layer region)) and ((" <100>" "[100]" "<110>" "[110]"))	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:47
S31	95	S19 and inverter and (insulat\$3 near (layer region)) and ((" <100>" "[100]" "<110>" "[110]")) and conductivity	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:53
S32	0	inverter and (insulat\$3 near (layer region)) and (orientation or crystal near orientation) and conductivity	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:53
S33	0	inverter and (insulat\$3 near (layer region)) and (orientation or crystal near orientation)	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:53
S34	1362	inverter and (insulat\$3 near (layer region)) and (orientation or crystal near orientation)	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:54
S35	732	inverter and (insulat\$3 near (layer region)) and (orientation or crystal near orientation) and conductivity	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:54
S36	215	inverter and (insulat\$3 near (layer region)) and (orientation or crystal near orientation) and conductivity and (PMOS PFET) and (NMOS NFET)	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:54
S37	10	("5789787").URPN.	USPAT	OR	ON	2006/02/20 18:01
S38	68975	CMOS	USPAT	OR	ON	2006/02/20 18:01
S39	13220	CMOS and (PMOS or PFET) and (NMOS or NFET)	USPAT	OR	ON	2006/02/20 19:19
S40	6654	CMOS and (PMOS or PFET) and (NMOS or NFET) and inverter	USPAT	OR	ON	2006/02/20 19:21
S41	1140	CMOS and (PMOS or PFET) and (NMOS or NFET) and inverter and interconnect	USPAT	OR	ON	2006/02/20 18:05
S42	277	CMOS and (PMOS or PFET) and (NMOS or NFET) and inverter and interconnect and orientation	USPAT	OR	ON	2006/02/20 18:06
S43	471	CMOS and (PMOS or PFET) and (NMOS or NFET) and inverter and interconnect and orientation	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 18:16
S44	1090	(crystal adj orientation surface adj orientation) and ([111] [110] [101] [100] [011] [010] [001] [000])	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 18:20
S45	21	inverter and (crystal adj orientation surface adj orientation) and ([111] [110] [101] [100] [011] [010] [001] [000])	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 18:32
S46	839	257/67	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 18:32

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S47	240	S46 and inverter	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 18:35
S48	74	S46 and inverter and orientation	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 18:38
S49	9	S46 and inverter and (("100" "110") near plane)	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 18:42
S50	9	S46 and inverter and (("100" "110") near (plane axis))	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 18:43
S51	348	inverter and (("100" "110") near (plane axis))	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 18:43
S52	236	semiconductor and inverter and (("100" "110") near (plane axis))	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 19:05
S53	1710	semiconductor and inverter and (lattice (("100" "110") near (plane axis)))	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 19:04
S54	3	inverter and miller adj indice	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 19:04
S55	626	semiconductor and miller adj indice	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 19:04
S56	195	semiconductor and miller adj indice and (("100" "110") near (plane axis))	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 19:13
S57	0	S41 and ("crystal direction" near3 ([100] [110]))	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 19:15
S58	2	S40 and ("crystal direction" near3 ([100] [110]))	US-PGPUB; USPAT; JPO	OR	ON	2006/02/20 19:15
S59	444	S46 and CMOS	USPAT	OR	ON	2006/02/20 19:26
S60	7	S59 and (NMOS PMOS) near5 (interconnection interconnected interconnecting)	USPAT	OR	ON	2006/02/20 19:27
S61	1	S60 and ("crystal direction" "crystal orientation")	USPAT	OR	ON	2006/02/20 19:27
S62	694	257/69	USPAT	OR	ON	2006/02/20 19:26
S63	397	S62 and CMOS	USPAT	OR	ON	2006/02/20 19:26
S64	2	S63 and (NMOS PMOS) near5 (interconnection interconnected interconnecting)	USPAT	OR	ON	2006/02/20 19:27
S65	0	S64 and ("crystal direction" "crystal orientation")	USPAT	OR	ON	2006/02/20 19:27

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S66	0	S64 and ("crystal direction" "crystal orientation" "crystal plane")	USPAT	OR	ON	2006/02/20 19:27
S67	779	257/903	USPAT	OR	ON	2006/02/20 19:28
S68	435	S67 and CMOS	USPAT	OR	ON	2006/02/20 19:28
S69	6	S67 and CMOS and (NMOS PMOS) near5 (interconnection interconnected interconnecting)	USPAT	OR	ON	2006/02/20 19:31
S70	1	S67 and CMOS and (NMOS PMOS) near5 (interconnection interconnected interconnecting) and ("crystal direction" "crystal orientation" "crystal plane")	USPAT	OR	ON	2006/02/20 19:29
S71	1139	257/57	USPAT	OR	ON	2006/02/20 19:29
S72	1	S71 and CMOS and (NMOS PMOS) near5 (interconnection interconnected interconnecting) and ("crystal direction" "crystal orientation" "crystal plane")	USPAT	OR	ON	2006/02/20 19:29
S73	522	438/152	USPAT	OR	ON	2006/02/20 19:29
S74	0	S73 and CMOS and (NMOS PMOS) near5 (interconnection interconnected interconnecting) and ("crystal direction" "crystal orientation" "crystal plane")	USPAT	OR	ON	2006/02/20 19:29
S75	484	257/904	USPAT	OR	ON	2006/02/20 19:29
S76	0	S75 and CMOS and (NMOS PMOS) near5 (interconnection interconnected interconnecting) and ("crystal direction" "crystal orientation" "crystal plane")	USPAT	OR	ON	2006/02/20 19:30
S77	2078	257/369	USPAT	OR	ON	2006/02/20 19:30
S78	0	S77 and CMOS and (NMOS PMOS) near5 (interconnection interconnected interconnecting) and ("crystal direction" "crystal orientation" "crystal plane")	USPAT	OR	ON	2006/02/20 19:30
S79	1612	438/199	USPAT	OR	ON	2006/02/20 19:30
S80	0	S79 and CMOS and (NMOS PMOS) near5 (interconnection interconnected interconnecting) and ("crystal direction" "crystal orientation" "crystal plane")	USPAT	OR	ON	2006/02/20 19:30
S81	1	S79 and CMOS and (NMOS PMOS) near5 (interconnection interconnected interconnecting) and crystal\$3	USPAT	OR	ON	2006/02/20 19:31
S82	1	S77 and CMOS and (NMOS PMOS) near5 (interconnection interconnected interconnecting) and crystal\$3	USPAT	OR	ON	2006/02/20 19:30

EAST Search History

S83	8	("5852310" "5949092" "5952678").PN. OR ("6204518").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 20:00
S84	8	("5852310" "5949092" "5952678").PN. OR ("6204518").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 20:11
S85	13	("5949092").URPN.	USPAT	OR	ON	2006/02/21 08:13
S86	1701	438/166	US-PGPUB; USPAT; JPO	OR	ON	2006/02/21 08:40
S87	460	438/150	US-PGPUB; USPAT; JPO	OR	ON	2006/02/21 08:53
S88	67801	yamazaki.in.	US-PGPUB; USPAT; JPO	OR	ON	2006/02/21 08:41
S89	4165	("semiconductor energy laboratory" sel).as.	US-PGPUB; USPAT; JPO	OR	ON	2006/02/21 08:53
S90	227	S87 and CMOS	US-PGPUB; USPAT; JPO	OR	ON	2006/02/21 09:12
S91	422	S89 and CMOS and inverter	US-PGPUB; USPAT; JPO	OR	ON	2006/02/21 08:53
S92	56	"4,933,298"	US-PGPUB; USPAT; JPO	OR	ON	2006/02/21 09:12
S93	26	("20020140031" "20030102518" "4768076" "4857986" "4933298" "5013681" "5024723" "5213986" "5374564" "5384473" "5659192" "5759898" "5769991" "5863830" "6335231" "6355541" "6358806" "6368938" "6407406" "6410371" "6414355" "6429061" "6448114" "6483171" "6486008" "6593634").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/21 09:15
S94	2	"20060043571"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 21:27
S95	4063	((257/700) or (257/713) or (257/701)).CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2006/07/23 21:48
S96	805	257/903	USPAT	OR	ON	2006/07/23 21:48
S97	8	S96 and CMOS and (NMOS PMOS) near5 (interconnection interconnected interconnecting)	USPAT	OR	ON	2006/07/23 21:48
S98	2199	257/369	USPAT	OR	ON	2006/07/23 21:48

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S99	717	257/69	USPAT	OR	ON	2006/07/23 21:48
S10 0	1740	438/199	USPAT	OR	ON	2006/07/23 21:48
S10 1	1	"20050098853"	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/05 10:11
S10 2	2	"20060043571"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/17 20:57
S10 3	2	"20060043571"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 14:30
S10 4	121	(upper and lower and cmos) same orientation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/01 10:47
S10 5	2	"20060275971"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/01 10:47
S10 6	81	(second near orientation) and PFET and NFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/03 18:07
S10 7	78	(second near orientation) and PFET and NFET	US-PGPUB; USPAT	OR	ON	2007/09/04 08:54
S10 8	89	(different near orientation) and PFET and NFET	US-PGPUB; USPAT	OR	ON	2007/09/03 18:24
S10 9	27836	(lower semiconductor device).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/09/04 09:03
S11 0	22005	(upper semiconductor device).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/09/04 09:03

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S11 1	4742	(second crystal orientation).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/09/04 09:01
S11 2	11182	(interconnect structure).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/09/04 09:01
S11 3	667	(pFET device nFET).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/09/04 09:01
S11 4	36769	(active region).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/09/04 09:02
S11 5	39741	(layer between lower upper).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/09/04 09:03
S11 6	1	S109 S110 S111 S112 S113 S114 S115	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/09/04 09:03
S11 7	146110	(upper device).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/09/04 09:03
S11 8	181473	(lower device).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/09/04 09:03
S11 9	1	S111 S112 S113 S114 S115 S117 S118	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/09/04 09:03

EAST Search History

S12 0	1436	(257/713).CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2007/09/04 09:04
S12 1	1373	(257/701).CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2007/09/04 09:04
S12 2	1910	(257/700).CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2007/09/04 09:04
S12 3	857	257/903	USPAT	OR	ON	2007/09/04 09:04
S12 4	620	438/150	US-PGPUB; USPAT; JPO	OR	ON	2007/09/04 09:05
S12 5	811	257/69	USPAT	OR	ON	2007/09/04 09:05

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L9	1	(lower semiconductor second crystal orientation [110] interconnect structure pFET nFET device).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/09/18 11:42